

AP9962AGH

RoHS-compliant Product

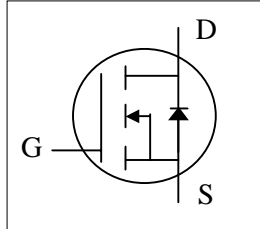


**Advanced Power
Electronics Corp.**

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

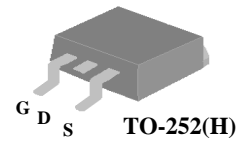
- ▼ Low On-resistance
- ▼ Single Drive Requirement
- ▼ Surface Mount Package



BV_{DSS}	40V
$R_{DS(ON)}$	20m Ω
I_D	32A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



The TO-252 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	32	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	20	A
I_{DM}	Pulsed Drain Current ¹	120	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	27.8	W
	Linear Derating Factor	0.22	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	4.5	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	$^\circ C/W$



Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	-	-	20	mΩ
		V _{GS} =4.5V, I _D =16A	-	-	30	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =20A	-	19	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =40V, V _{GS} =0V	-	-	10	uA
	Drain-Source Leakage Current (T _j =150°C)	V _{DS} =32V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =20A	-	12	20	nC
Q _{gs}	Gate-Source Charge	V _{DS} =32V	-	2.7	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	7.8	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =20V	-	7	-	ns
t _r	Rise Time	I _D =20A	-	46	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	20	-	ns
t _f	Fall Time	R _D =1.0Ω	-	6	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	820	1800	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	95	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	90	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =32A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time	I _S =10A, V _{GS} =0V,	-	19	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	13	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

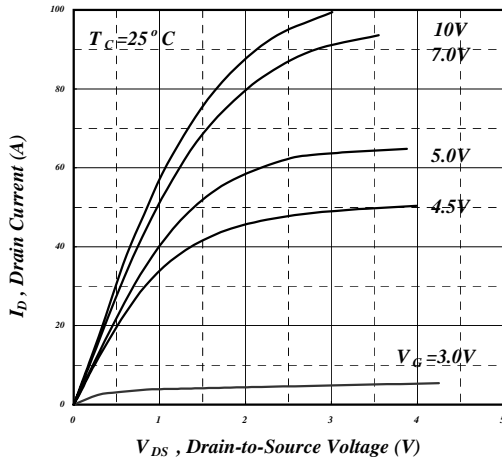


Fig 1. Typical Output Characteristics

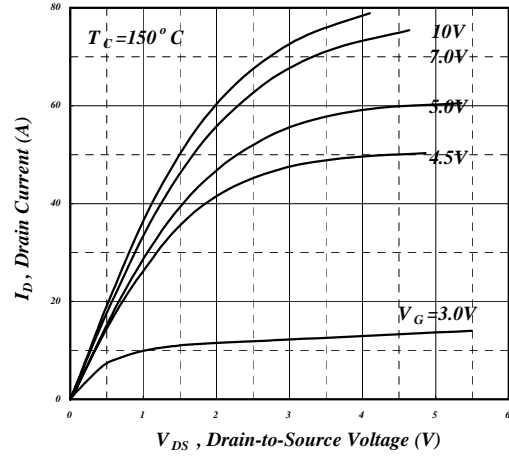


Fig 2. Typical Output Characteristics

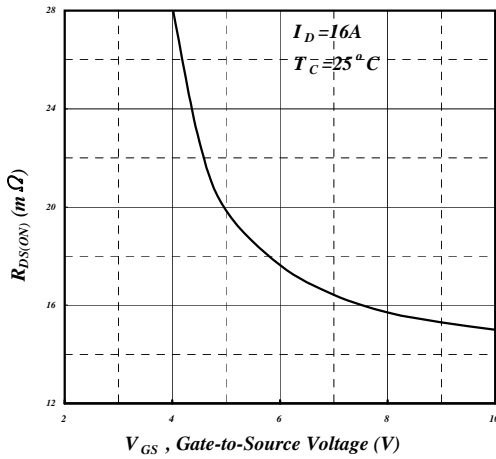


Fig 3. On-Resistance v.s. Gate Voltage

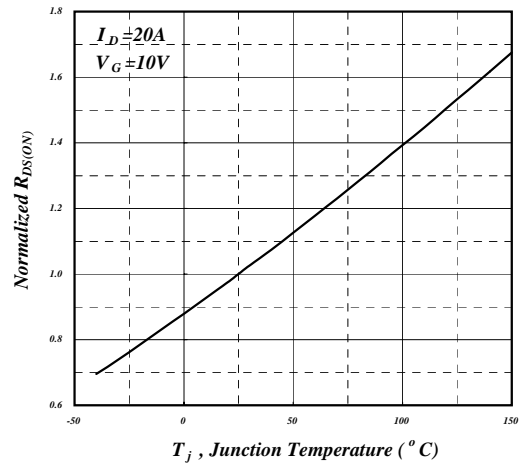


Fig 4. Normalized On-Resistance v.s. Junction Temperature

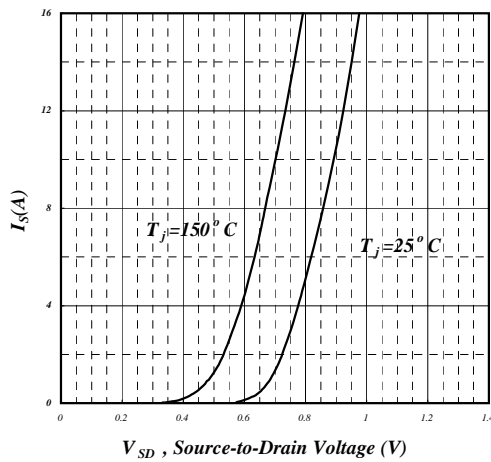


Fig 5. Forward Characteristic of Reverse Diode

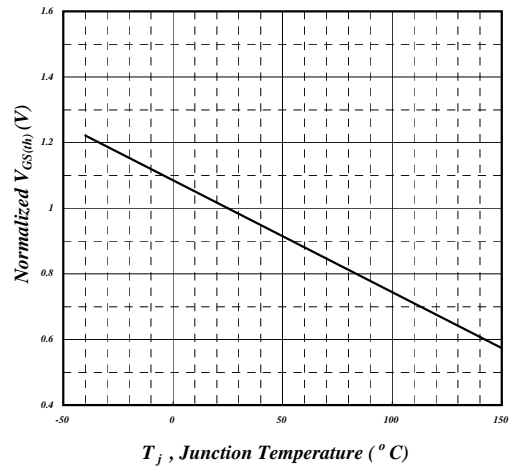


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

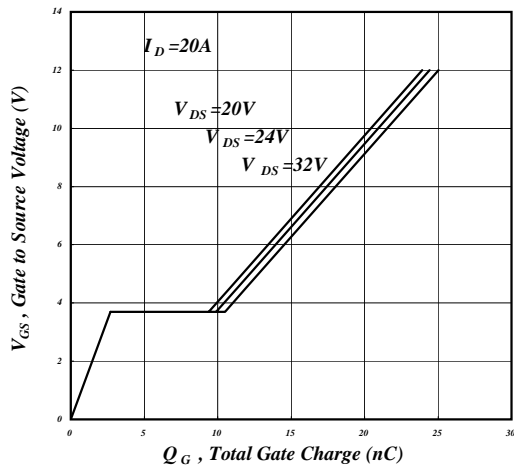


Fig 7. Gate Charge Characteristics

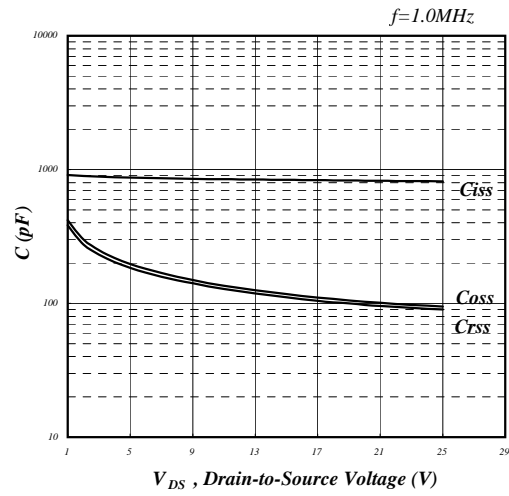


Fig 8. Typical Capacitance Characteristics

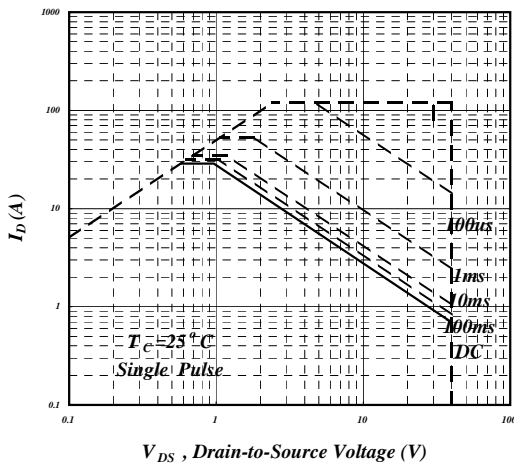


Fig 9. Maximum Safe Operating Area

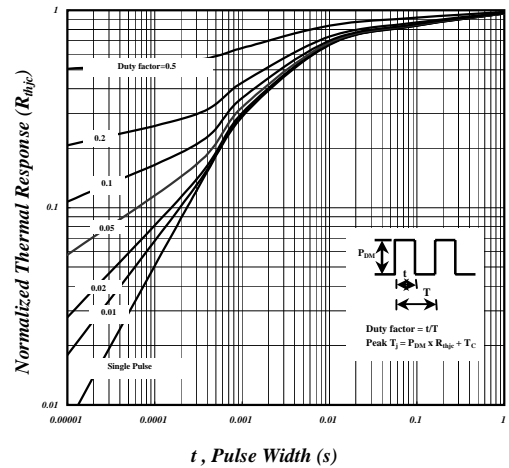


Fig 10. Effective Transient Thermal Impedance

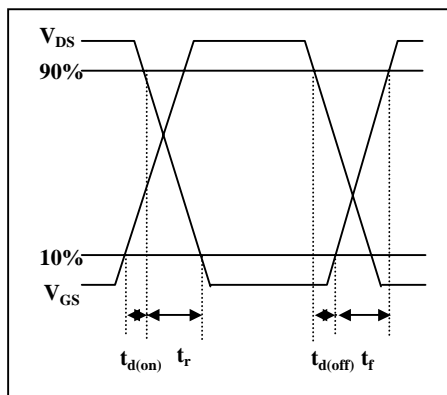


Fig 11. Switching Time Waveform

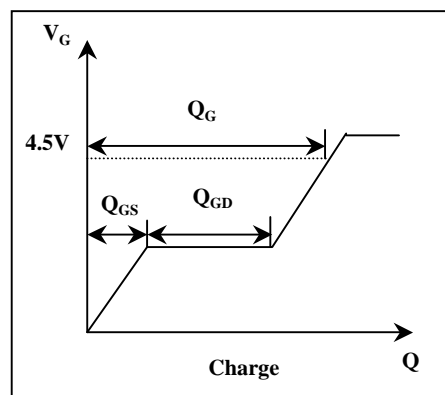
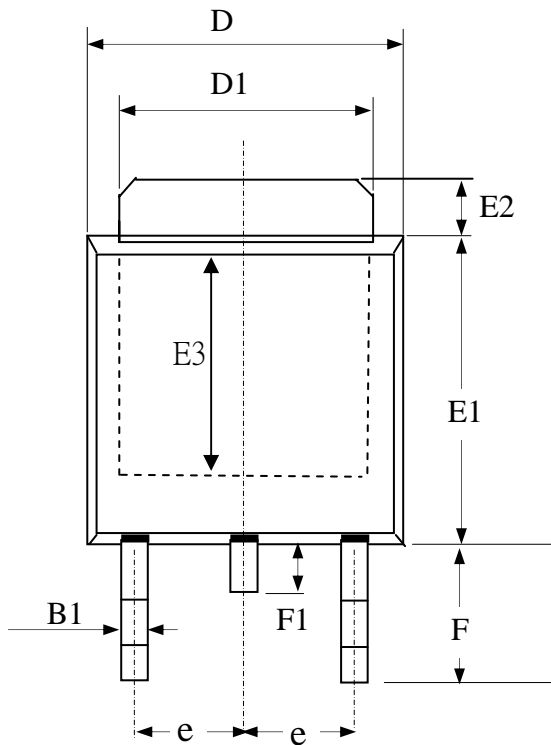


Fig 12. Gate Charge Waveform

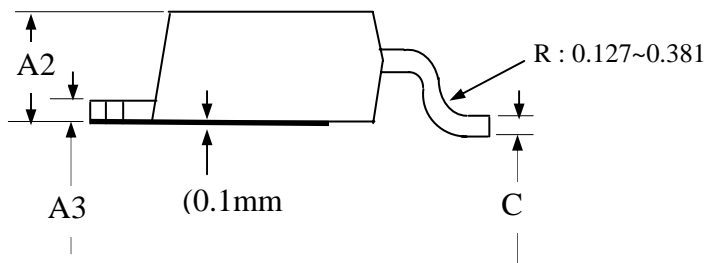


Package Outline : TO-252

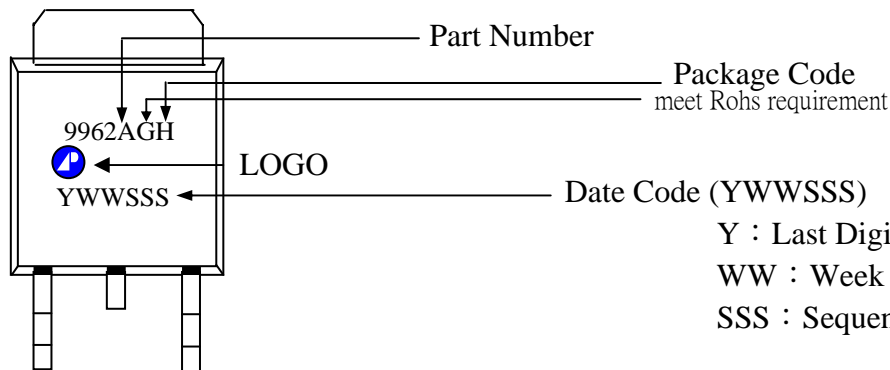


SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.5	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.



Part Marking Information & Packing : TO-252



Y : Last Digit Of The Year
 WW : Week
 SSS : Sequence